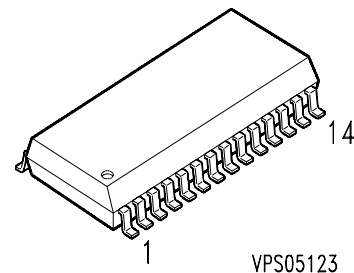
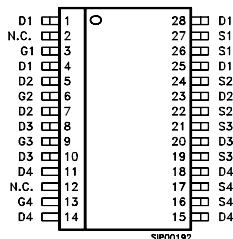


SIPMOS[®] Power Transistor

- Quad-channel
- Enhancement mode
- Avalanche-rated
- dv/dt rated



Type	V_{DS}	I_D	$R_{DS(on)}$	Package	Ordering Code
BUZ 100S-4	55 V	8 A	0.02 Ω	P-DSO-28	C67078-S. . . . -A..

Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current <i>one channel active</i> $T_A = 25\text{ }^\circ\text{C}$	I_D	8	A
Pulsed drain current <i>one channel active</i> $T_A = 25\text{ }^\circ\text{C}$	I_{Dpuls}	32	A
Avalanche energy, single pulse $I_D = 8\text{ A}$, $V_{DD} = 25\text{ V}$, $R_{GS} = 25\text{ }\Omega$ $L = 11.8\text{ mH}$, $T_j = 25\text{ }^\circ\text{C}$	E_{AS}	380	mJ
Reverse diode dv/dt $I_S = 8\text{ A}$, $V_{DS} = 40\text{ V}$, $di_F/dt = 200\text{ A}/\mu\text{s}$ $T_{jmax} = 175\text{ }^\circ\text{C}$	dv/dt	6	kV/ μs
Gate source voltage	V_{GS}	± 20	V
Power dissipation , <i>one channel active</i> $T_A = 25\text{ }^\circ\text{C}$	P_{tot}	2.4	W
Operating temperature	T_j	-55 ... + 175	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ... + 175	$^\circ\text{C}$
IEC climatic category, DIN IEC 68-1		55 / 175 / 56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - soldering point ¹⁾	R_{thJS}	-	-	tbd	K/W
Thermal resistance, junction - ambient ²⁾	R_{thJA}	-	-	62.5	

1) Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm² (one layer, 70μm thick) copper area for Drain connection. PCB is vertical without blown air.

2) one channel active

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Drain- source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 0.25\text{ mA}$, $T_j = 25^\circ\text{C}$	$V_{(BR)DSS}$	55	-	-	V
Gate threshold voltage $V_{GS}=V_{DS}$, $I_D = 130\text{ }\mu\text{A}$	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS} = 55\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = -40^\circ\text{C}$ $V_{DS} = 55\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25^\circ\text{C}$ $V_{DS} = 55\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 150^\circ\text{C}$	I_{DSS}	- - -	- 0.1 -	0.1 1 100	μA
Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	-	10	100	
Drain-Source on-resistance $V_{GS} = 10\text{ V}$, $I_D = 8\text{ A}$	$R_{DS(on)}$	-	0.016	0.02	Ω

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS} \geq 2 * I_D * R_{DS(on)max}$, $I_D = 8\text{ A}$	g_{fs}	15	-	-	S
Input capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	-	1900	2375	pF
Output capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	-	615	770	
Reverse transfer capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	-	310	390	
Turn-on delay time $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 8\text{ A}$ $R_G = 4.6\text{ }\Omega$	$t_{d(on)}$	-	25	40	ns
Rise time $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 8\text{ A}$ $R_G = 4.6\text{ }\Omega$	t_r	-	25	40	
Turn-off delay time $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 8\text{ A}$ $R_G = 4.6\text{ }\Omega$	$t_{d(off)}$	-	75	115	
Fall time $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 8\text{ A}$ $R_G = 4.6\text{ }\Omega$	t_f	-	35	55	
Gate charge at threshold $V_{DD} = 40\text{ V}$, $I_D \geq 0.1\text{ A}$, $V_{GS} = 0\text{ to }1\text{ V}$	$Q_{g(th)}$	-	3.8	5.7	nC
Gate charge at 7.0 V $V_{DD} = 40\text{ V}$, $I_D = 8\text{ A}$, $V_{GS} = 0\text{ to }7\text{ V}$	$Q_{g(7)}$	-	50	75	
Gate charge total $V_{DD} = 40\text{ V}$, $I_D = 8\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$	$Q_{g(total)}$	-	63	95	
Gate plateau voltage $V_{DD} = 40\text{ V}$, $I_D = 8\text{ A}$	$V_{(plateau)}$	-	4.43	-	V

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

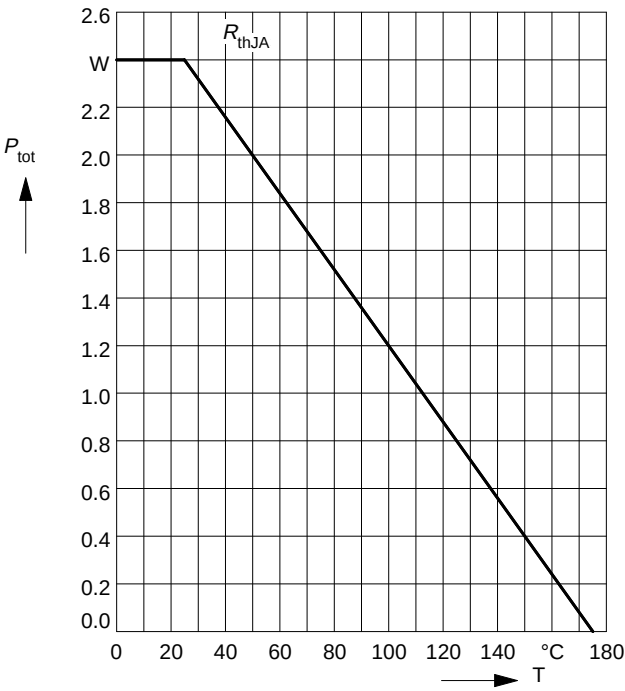
Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Reverse Diode

Inverse diode continuous forward current $T_A = 25^\circ\text{C}$	I_S	-	-	8	A
Inverse diode direct current, pulsed $T_A = 25^\circ\text{C}$	I_{SM}	-	-	32	
Inverse diode forward voltage $V_{GS} = 0\text{ V}$, $I_F = 16\text{ A}$	V_{SD}	-	0.95	1.6	V
Reverse recovery time $V_R = 30\text{ V}$, $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	70	105	ns
Reverse recovery charge $V_R = 30\text{ V}$, $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	0.2	0.3	μC

Power dissipation

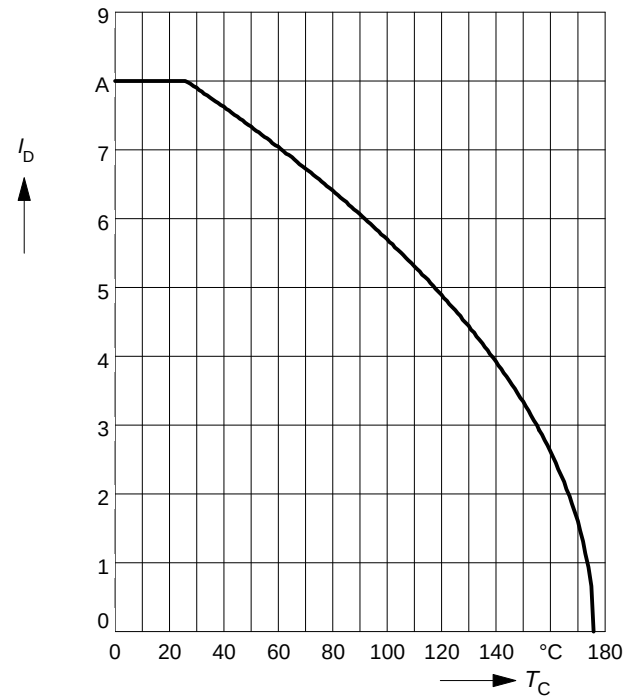
$P_{\text{tot}} = f(T)$



Drain current

$I_D = f(T_C)$

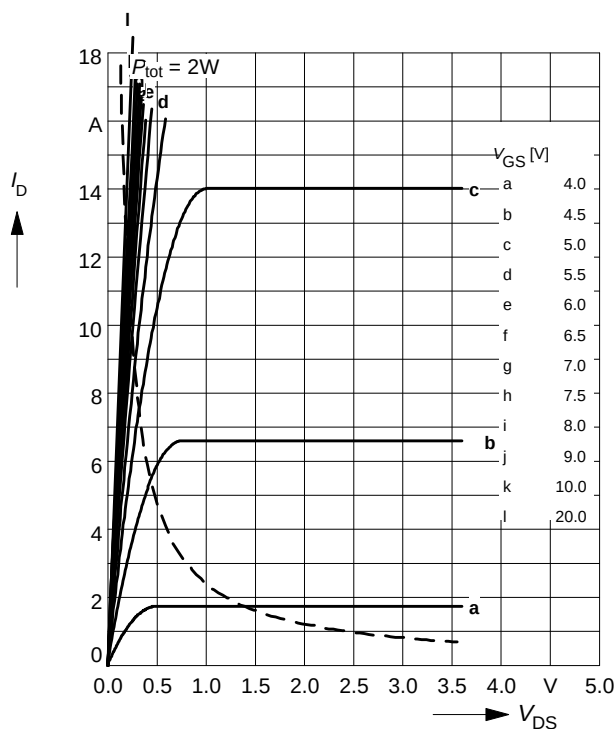
parameter: $V_{\text{GS}} \geq 10$ V



Typ. output characteristics

$$I_D = f(V_{DS})$$

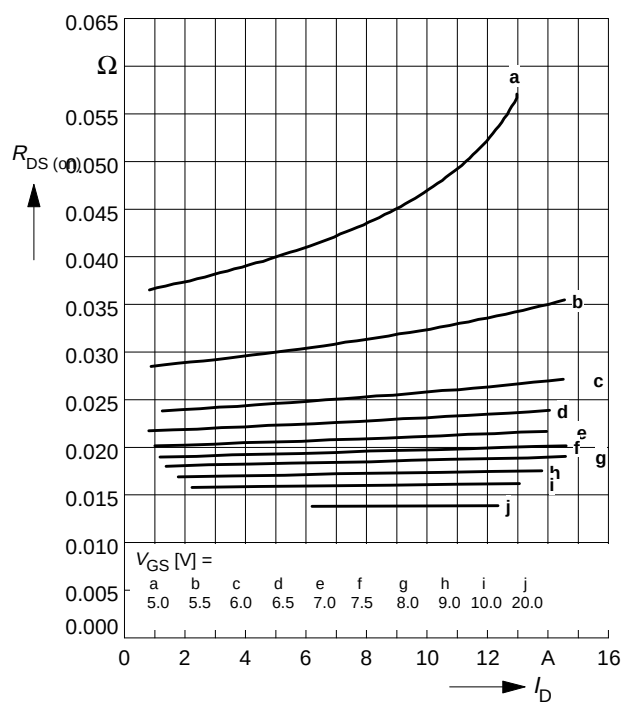
parameter: $t_p = 80 \mu s$



Typ. drain-source on-resistance

$$R_{DS(on)} = f(I_D)$$

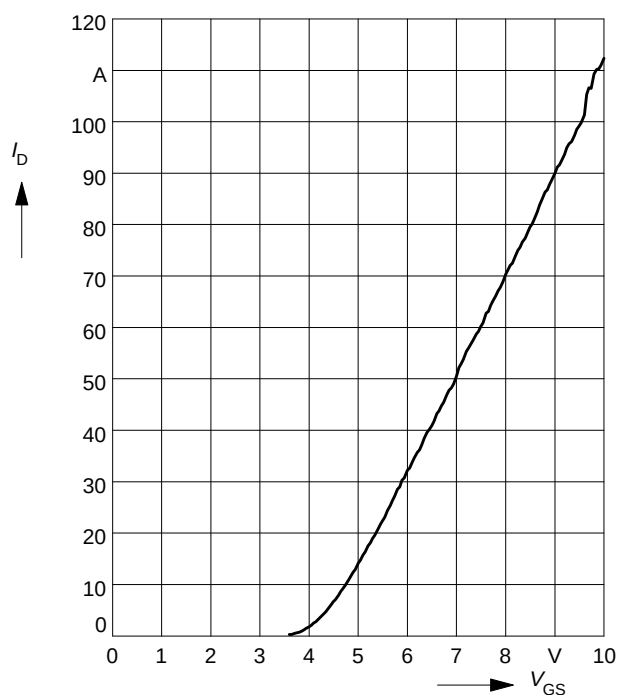
parameter: $t_p = 80 \mu s$, $T_j = 25^\circ C$



Typ. transfer characteristics $I_D = f(V_{GS})$

parameter: $t_p = 80 \mu s$

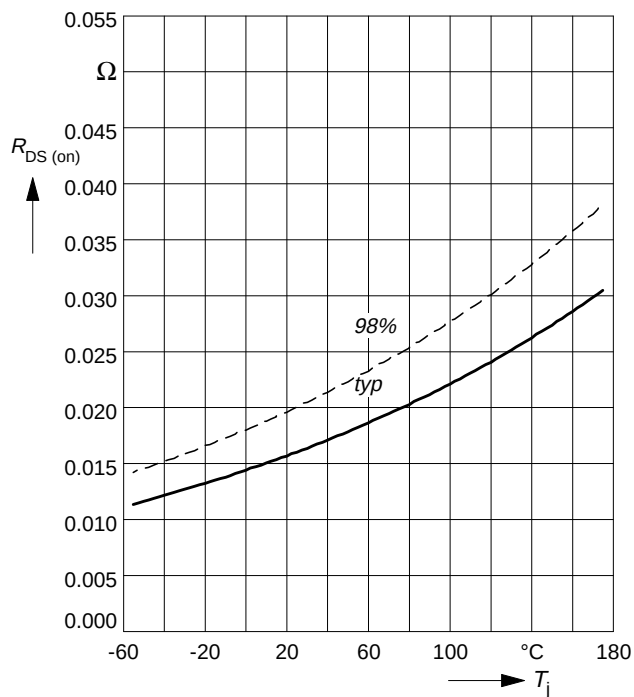
$$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$



Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

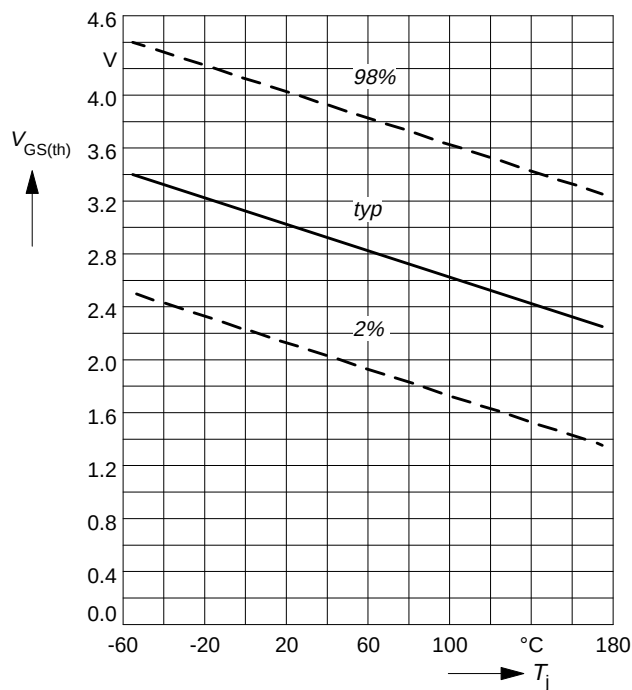
parameter: $I_D = 8\text{ A}$, $V_{GS} = 10\text{ V}$



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

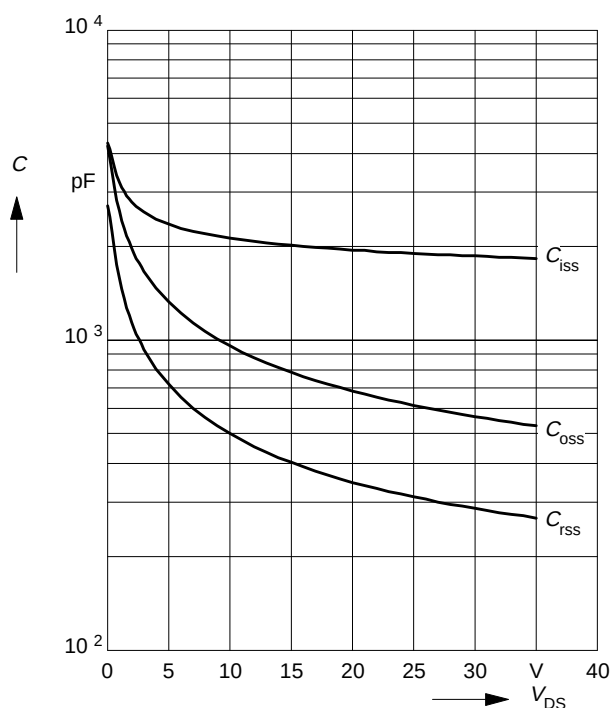
parameter: $V_{GS} = V_{DS}$, $I_D = 130\text{ }\mu\text{A}$



Typ. capacitances

$$C = f(V_{DS})$$

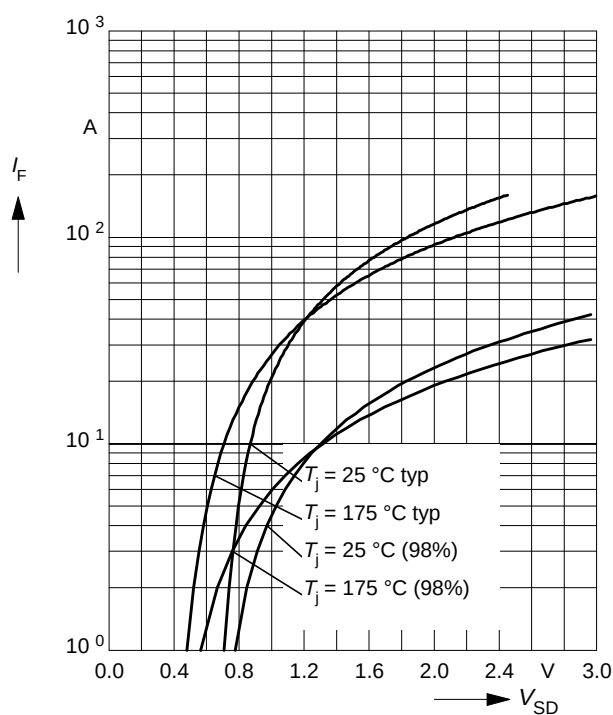
parameter: $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$



Forward characteristics of reverse diode

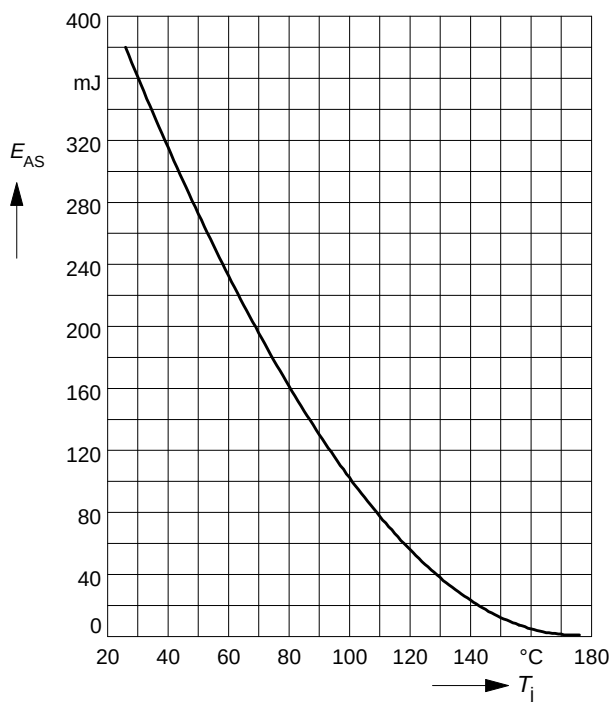
$$I_F = f(V_{SD})$$

parameter: T_j , $t_p = 80\text{ }\mu\text{s}$



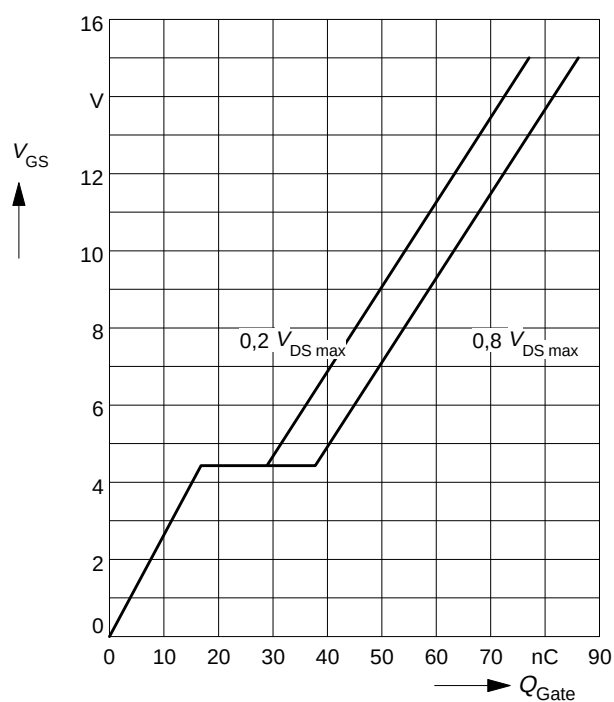
Avalanche energy $E_{AS} = f(T_j)$

parameter: $I_D = 8\text{ A}$, $V_{DD} = 25\text{ V}$
 $R_{GS} = 25\ \Omega$, $L = 11.8\text{ mH}$



Typ. gate charge

$V_{GS} = f(Q_{Gate})$
 parameter: $I_{D\text{ puls}} = 8\text{ A}$



Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$

